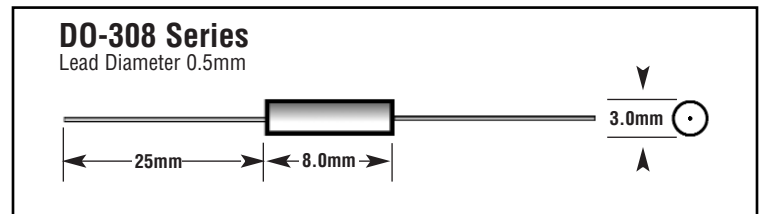
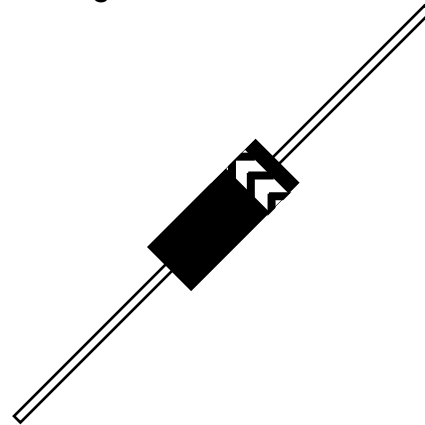




High reliability resin molded type high voltage diode in small size package which is sealed a multilayered mesa type silicon chip by epoxy resin.

Outline Drawings :



Features

- High speed switching
- Epoxy resin molded in vacuum, Have anticorrosion in the surface
- High surge resistivity for CRT discharge
- High reliability design
- Avalanche characteristic

Applications

- X light Power supply
- Laser
- Voltage doubler circuit
- Microwave emission power
- General purpose high voltage rectifier, Voltage multiplier assembly.

Maximum Ratings and Characteristics

- Absolute Maximum Ratings

Items	Symbols	Condition	HV10G06	Units
Repetitive Peak Reverse Voltage	V_{RRM}	$T_a=25^{\circ}C,$	6.0	kV
Average Output Current	I_o	$T_a=25^{\circ}C,$ Resistive Load	10	mA
Surge Current	I_{FSM}	$T_a=25^{\circ}C, 8.3\text{ ms}$	1.0	A _{peak}
Junction Temperature	T_j		125	$^{\circ}C$
Allowable Operation Case Temperature	T_c		125	$^{\circ}C$
Storage Temperature	T_{stg}		-40 to +125	$^{\circ}C$

- Electrical Characteristics ($T_a=25^{\circ}C$ Unless otherwise specified)

Items	Symbols	Conditions	HV10G06	Units
Maximum Forward Voltage Drop	V_F	at $25^{\circ}C, I_F = I_{F(AV)}$	20	V
Maximum Reverse Current	IR1	at $25^{\circ}C, V_R = V_{RRM}$	2.0	μA
	IR2	at $100^{\circ}C, V_R = V_{RRM}$	5.0	μA
Maximum Reverse Recovery Time	T_{rr}	at $25^{\circ}C; I_F = 2mA; I_R = 4mA; I_{rr} = 1mA;$	100	nS
Junction Capacitance	C_j	at $25^{\circ}C; V_R = 0V, f = 1MHz$	1.0	pF

■ Typical characteristics:

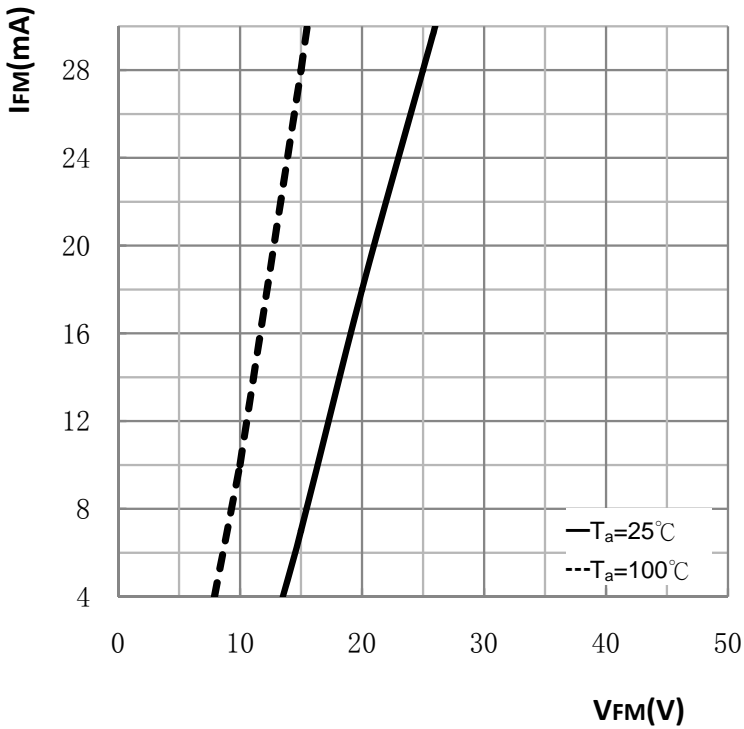


Figure 1. Forward characteristics

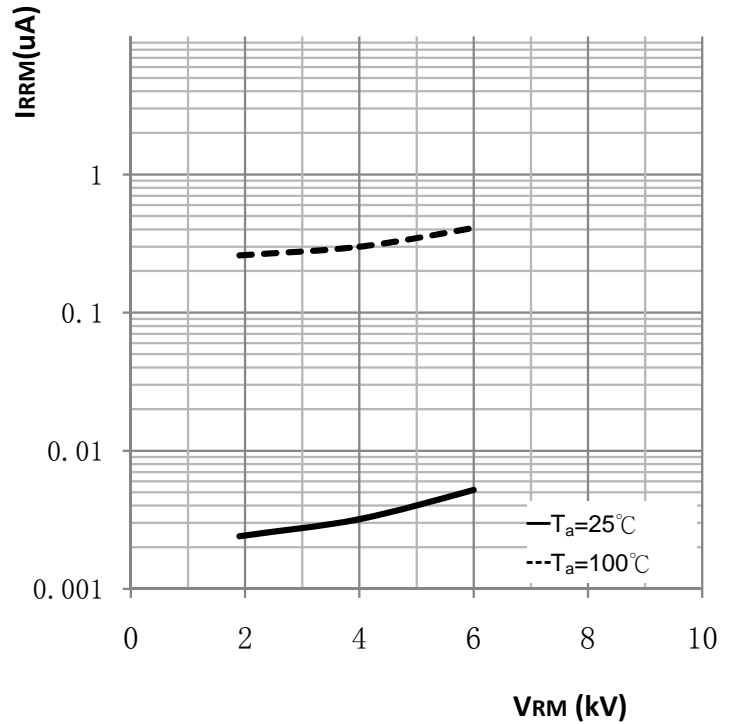


Figure 2. Reverse characteristics

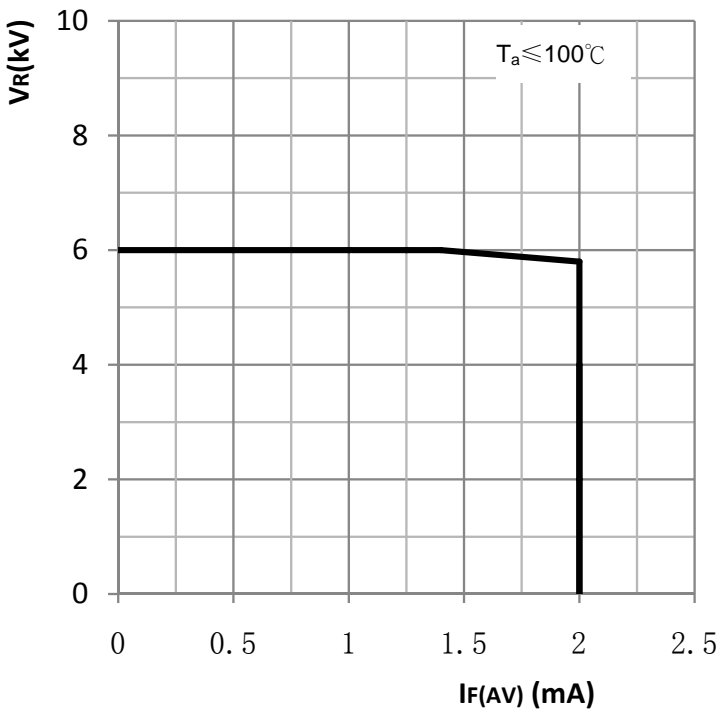


Figure 3. $V_R - I_{F(AV)}$ Curve

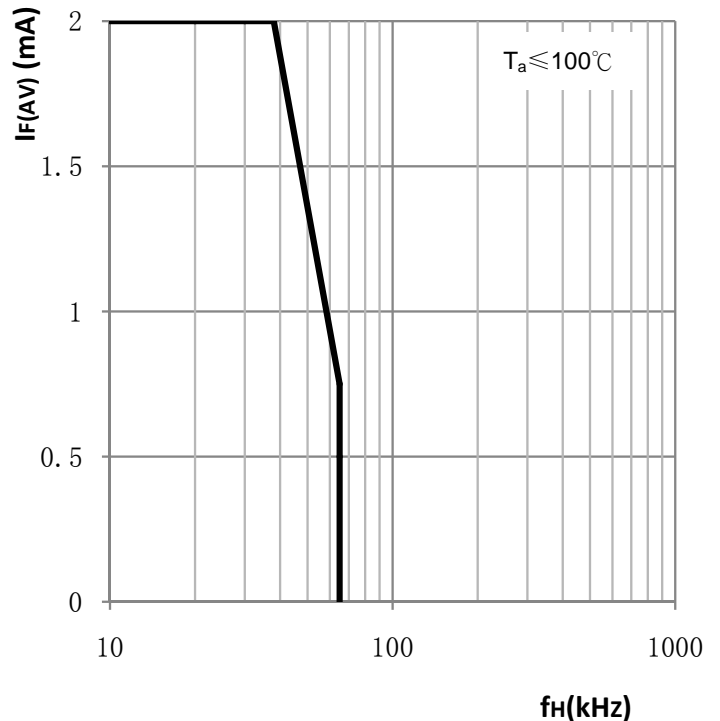


Figure 4. $I_{F(AV)} - f_H$ Curve